



National
Semiconductor™

Pro Electron Bipolar Devices

Pro Electron Series

Discrete **POWER & Signal**
Technologies

Device No.	Case Style	V _{CES} [*] V _{CBO} (V) Min	V _{CEO} (V) Min	V _{EBD} (V) Min	I _{CBO} (nA) Max	V _{CB} (V) Max	H _{FE} h _{FE} Min Max	I _C & V _{CE} (mA) (V)	V _{CE(SAT)} (V) Max	V _{BE(SAT)} & V _{BE(ON)} [*] (V) Min Max	I _C (mA) Max	C _{ob} (pF) Max	f _T (MHz) Min Max	I _C (mA) Max	NF (dB) Max	Test Conditions	Process No.
BC327	TO-92 (97)	50*	45	5	100*	45	40 100	300 100	0.7	1.2*	500 300						67
BC327A	TO-92 (97)	60*	60	5	100*	45	40 100	300 100	0.7	1.2*	300 500						67
BC327-16	TO-92 (97)	50*	45	5	100*	45	40 100	300 100	0.7	1.2*	500 300						67
BC327-25	TO-92 (97)	50*	45	5	100*	45	40 160	300 100	0.7	1.2*	500 300						67
BC328	TO-92 (97)	30*	25	5	100*	25	40 100	100 100	0.7	1.2	500 300						67
BC328-25	TO-92 (97)	30*	25	5	100*	25	40 160	100 100	0.7	1.2	500 300						67
BC337	TO-92 (97)	50*	45	5	100	20	100 40	600 500	0.7	500	500						12
BC337A	TO-92 (97)	60*	60	5	100	20	100 40	600 500	0.7	500	500						12
BC337-16	TO-92 (97)	50*	45	5	100	20	100 40	250 500	0.7	500	500						12
BC337-25	TO-92 (97)	50*	45	5	100	20	160 40	400 500	0.7	500	500						12
BC338	TO-92 (97)	30*	20	5	100	20	100 40	600 500	0.7	500	500						12
BC368	TO-92 (94)	25*	20	5	10K	25	50 85 60	5 375 1A	0.5	1A	1A		40	10			37 (6-1)

NOTE: National preferred device for each process in **bold**. Number shown in parentheses indicates location (section-page) of device datasheet.